

# **NDT3055**

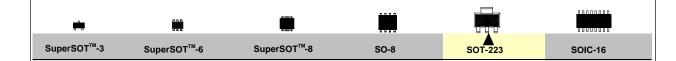
# N-Channel Enhancement Mode Field Effect Transistor

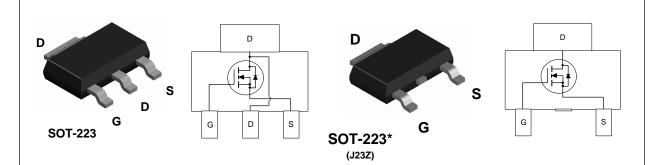
### **General Description**

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

### **Features**

- $\blacksquare$  4 A, 60 V.  $R_{\text{DS(ON)}}$  = 0.100  $\Omega$  @  $V_{\text{GS}}$  = 10 V.
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability in a widely used surface mount package.





# **Absolute Maximum Ratings** $T_A = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter		NDT3055	Units
V <sub>DSS</sub>	Drain-Source Voltage		60	V
V <sub>GSS</sub>	Gate-Source Voltage - Continuous		±20	V
I <sub>D</sub>	Maximum Drain Current - Continuo	US (Note 1a)	4	A
	- Pulse	d	25	
P <sub>D</sub>	P <sub>D</sub> Maximum Power Dissipation	(Note 1a)	3	W
		(Note 1b)	1.3	
		(Note 1c)	1.1	
T <sub>J</sub> ,T <sub>STG</sub>	Operating and Storage Temperatur	e Range	-65 to 150	°C
THERMA	L CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistance, Junction-to-A	mbient (Note 1a)	42	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-C	ase (Note 1)	12	°C/W
* Order or	ation 1237 for cropped center drain le	ad		

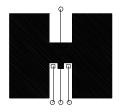
<sup>\*</sup> Order option J23Z for cropped center drain lead.

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		60			V
$\Delta$ BV <sub>DSS</sub> / $\Delta$ T <sub>J</sub>	Breakdown Voltage Temp. Coefficient	$I_D = 250 \mu A$ , Referenced to	25°C		63		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$				10	μA
			T <sub>J</sub> =125°C			100	μA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHARAC	CTERISTICS (Note 2)						
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2	3	4	V
			T <sub>J</sub> =125°C	1.5	2.4	3	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 4 \text{ A}$			0.084	0.1	Ω
			T <sub>J</sub> =125°C		0.14	0.18	
D(ON)	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$		15			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 4 \text{ A}$			6		S
DYNAMIC C	HARACTERISTICS						
Ciss	Input Capacitance	$V_{DS} = 30 \text{ V}, \ V_{GS} = 0 \text{ V}, $ f = 1.0 MHz	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$				pF
Coss	Output Capacitance	f = 1.0 MHz			100		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				30		pF
SWITCHING	CHARACTERISTICS (Note 2)						
D(on)	Turn - On Delay Time	$V_{DD} = 25 \text{ V}, I_{D} = 1.2 \text{ A},$					ns
r	Turn - On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 50 \Omega$			18	50	ns
D(off)	Turn - Off Delay Time				37	65	ns
f	Turn - Off Fall Time				30	60	ns
$Q_g$	Total Gate Charge	$V_{DS} = 40 \text{ V}, I_{D} = 4 \text{ A},$		9	15	nC	
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10 V			2.3		nC
$Q_{gd}$	Gate-Drain Charge				2.6		nC
)RAIN-SOU	RCE DIODE CHARACTERISTICS AND MA	XIMUM RATINGS					
S	Maximum Continuous Drain-Source Diode F				2.5	Α	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.5 \text{ A}$ (Note	2)		0.85	1.2	V

Notes:

the drain pins.  $\boldsymbol{R}_{\boldsymbol{\theta}^{JC}}$  is

Typical  $R_{\rm gul}$  using the board layouts shown below on FR-4 PCB in a still air environment:



a. 42°C/W when mounted on a 1 in² pad of 2oz Cu.



pad of 2oz Cu.

b. 95°C/W when mounted on a 0.066 in<sup>2</sup> c. 110°C/W when mounted on a 0.00123 in² pad of 2oz Cu.

Scale 1: 1 on letter size paper 2. Pulse Test: Pulse Width  $\leq 300 \mu s,$  Duty Cycle  $\leq 2.0\%$ 

<sup>1.</sup>  $R_{g,\mu}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of guaranteed by design while  $\boldsymbol{R}_{\theta \text{CA}}$  is determined by the user's board design.

# **Typical Electrical Characteristics**

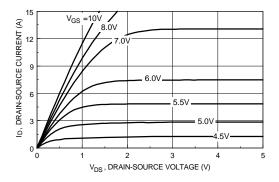


Figure 1. On-Region Characteristics.

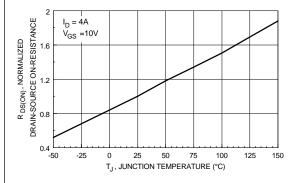


Figure 3. On-Resistance Variation with Temperature.

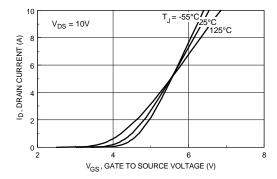


Figure 5. Transfer Characteristics.

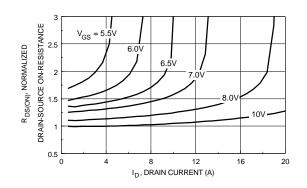


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

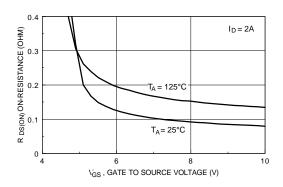


Figure 4. On-Resistance Variation with Gate-to- Source Voltage.

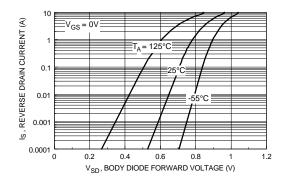


Figure 6. Body Diode Forward Voltage Variation with Current and Temperature.

# **Typical Electrical Characteristics (continued)**

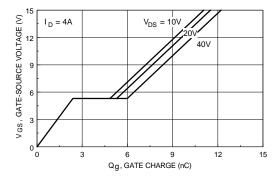
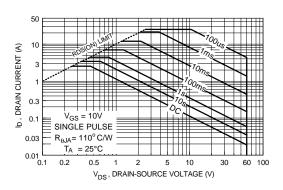


Figure 7. Gate Charge Characteristics.



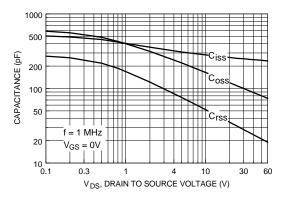


Figure 8. Capacitance Characteristics.

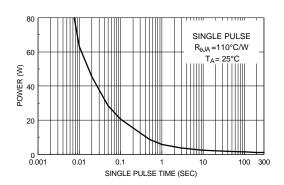


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

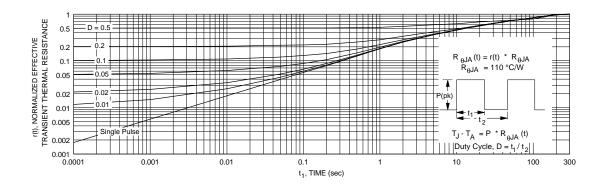


Figure 11. Transient Thermal Response Curve.

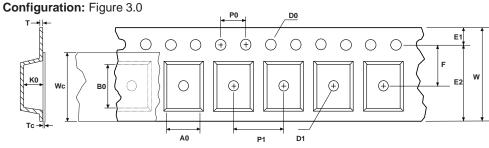
Thermal characterization performed using the conditions described in note 1c.

Transient thermal response will change depending on the circuit board design.





# **SOT-223 Embossed Carrier Tape**



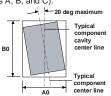
User Direction of Feed	
	$\overline{}$

	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
<b>SOT-223</b> (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



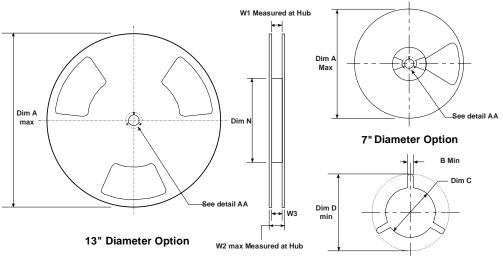
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

DETAIL AA

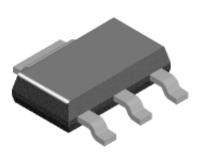
# SOT-223 Reel Configuration: Figure 4.0

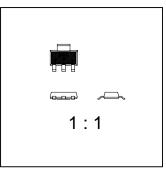


	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	

# SOT-223 Tape and Reel Data and Package Dimensions, continued

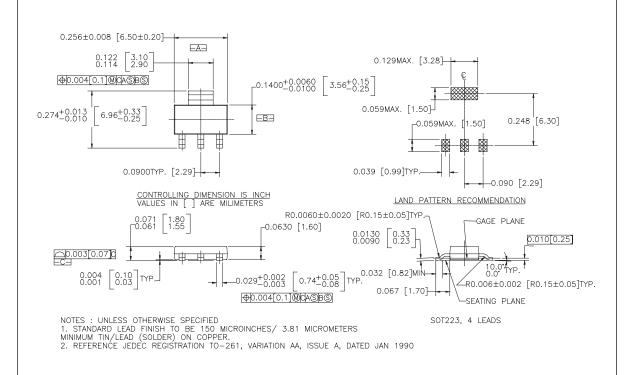
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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